

Rev.E Mar-2016

SOT-323

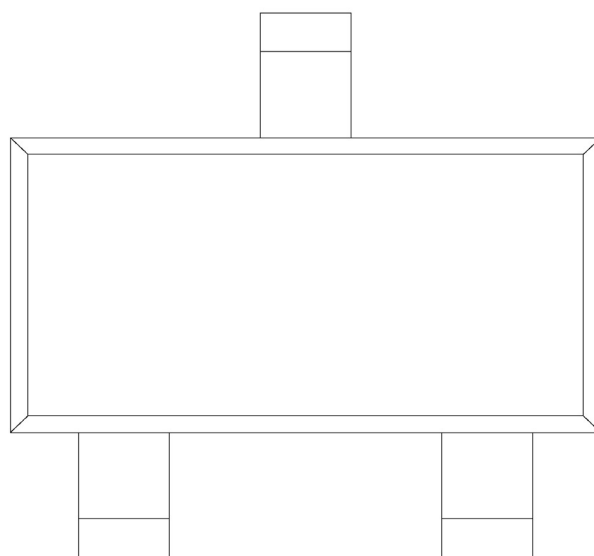
NPN

Silicon NPN transistor in



Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	50	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=50\mu A$	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$	25			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=50\mu A$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=24V$			0.5	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=3.0V$			0.5	μA
DC Current Gain	h_{FE}	$V_{CE}=6.0V$ $I_C=1.0mA$	56		270	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA$ $I_B=1.0mA$		0.1	0.3	V
Transition Frequency	f_T	$V_{CE}=6.0V$ $f=100MHz$ $I_C=1.0mA$	150	300		MHz
Collector output capacitance	C_{ob}	$V_{CB}=6.0V$ $f=1.0MHz$ $I_E=0$		1.3	2.2	pF



H

A

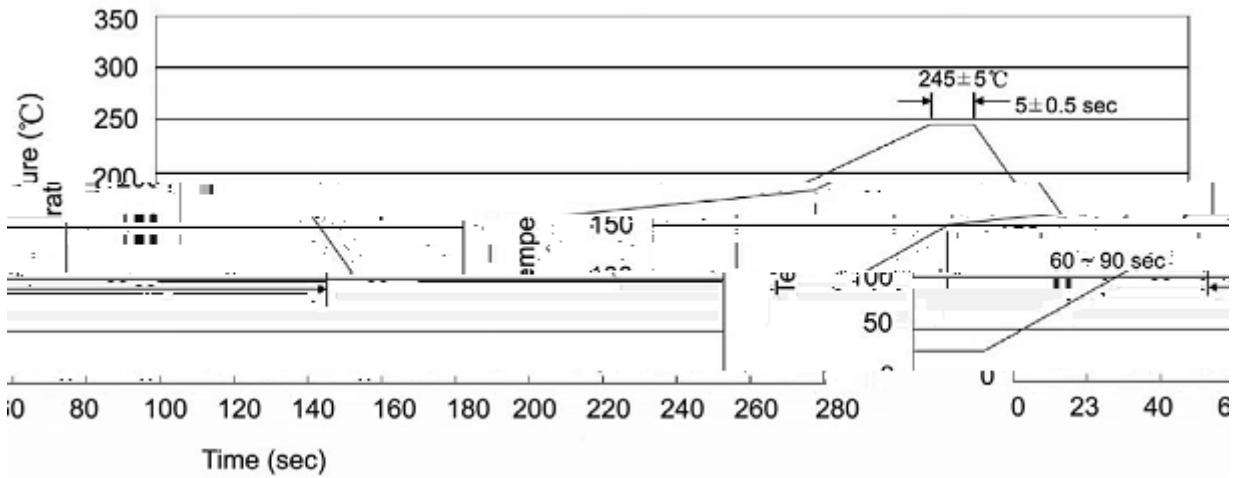
N h_{FE}

Note:

H: Company Code.

A: Product Type.

N h_{FE}



Note:

- | | | | | | |
|---|-------|-----|----|-----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245±5 | | | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

 260 ± 5
 $10 \pm 1 \text{ sec.}$

 Temp.: 260 ± 5

 Time: $10 \pm 1 \text{ sec}$

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-323	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205